Circ							
Comparison of the comparison	1	Hits	Search Query	DBs	l .	Plurals	Time Stamp
Solidification) sis	L2	2		USPAT;	OR	OFF	2005/02/18 14:10
L11	L9	24804			OR	ON	2005/02/18 14:16
Solidification) sls	L10	119	9 same mask same laser		OR	ON	2005/02/18 16:30
L18	L11	415		DERWENT;	OR .	OFF	2005/02/18 14:17
257/75.ccls. 257/e21.134.ccls. 430/5.ccls. 438/947.ccls. 438/943. ccls. 438/946.ccls.	L12	25	11 and mask and laser	DERWENT;	OR	ON	2005/02/18 14:18
L20 1086 18 and (mask with laser) USPAT US-PGPUB; OR USPAT US-PGPUB; USPAT US-PGPUB; USPAT USP	L18	6477	257/75.ccls. 257/e21.134.ccls. 430/5.ccls. 438/487.ccls. 438/943.		OR	OFF	2005/02/18 16:33
L21 972 20 and (crystall\$10 semiconductor silicon polysilicon polycrystalline (grain adj growth) amorphous) US-PGPUB; USPAT US-PGPUB; USPAT; EPO; JPO; DERWENT US-PGPUB; US-P	L19	101	9 and 18	1	OR	ON	2005/02/18 17:25
Silicon polysilicon polycrystalline (grain adj growth) amorphous) USPAT	L20	1086	18 and (mask with laser)	1	OR	ON	2005/02/18 16:34
Crystall\$10 semiconductor silicon polysilicon polycrystalline (grain adj growth) amorphous))	L21	972	silicon polysilicon polycrystalline		OR	ON	2005/02/18 16:36
L24 257 18 and (mask with laser with (crystall\$10 semiconductor silicon polysilicon polycrystalline (grain adj growth) amorphous)) US-PGPUB; OR ON 2005/02/18 17:3 L24 257 18 and (mask with laser with (crystall\$10 semiconductor silicon polysilicon polycrystalline (grain adj growth) amorphous)) US-PGPUB; OR OFF 2005/02/18 17:3 L25 1 1999kr-0047533.ap,prai. US-PGPUB; US-PGPUB; OR OFF 2005/02/18 17:3 L26 1 2001-588384.NRAN. DERWENT OR OFF 2005/02/18 17:3 S1 2 "20040259296".pn. "20030040146".pn. US-PGPUB; OR OFF 2005/02/16 17:4 S2 2 "6755909".pn. "6792029".pn. US-PGPUB; OR OFF 2005/02/16 17:4	L22	672	(crystall\$10 semiconductor silicon polysilicon polycrystalline (grain	1	OR	ON	2005/02/18 16:38
(crystall\$10 semiconductor silicon polysilicon polysilicon polycrystalline (grain adj growth) amorphous)) L25 1 1999kr-0047533.ap,prai. US-PGPUB; US-PGPUB; US-PGPUB; US-PGPUB; US-PGPUB; US-PGPUB; US-PGPUB; US-PGPUB; US-PGPUB; OR US-PGPUB; OR US-PGPUB; US-PGPUB; US-PGPUB; US-PGPUB; US-PGPUB; US-PGPUB; US-PGPUB; US-PGPUB; OR US-PGPUB; OR OFF 2005/02/16 17:40	L23	416	(crystall\$10 semiconductor silicon polysilicon polycrystalline (grain	1	OR	ON	2005/02/18 16:37
USPAT; EPO; JPO; DERWENT L26 1 2001-588384.NRAN. DERWENT OR OFF 2005/02/18 17:3 S1 2 "20040259296".pn. "20030040146".pn. US-PGPUB; USPAT USPAT S2 2 "6755909".pn. "6792029".pn. US-PGPUB; OR OFF 2005/02/16 17:4	L24	257	(crystall\$10 semiconductor silicon polysilicon polycrystalline (grain		OR	ON	2005/02/18 17:32
S1 2 "20040259296".pn. US-PGPUB; USPAT OFF 2005/02/16 17:4 S2 2 "6755909".pn. "6792029".pn. US-PGPUB; OR OFF 2005/02/16 17:4	L25	1	1999kr-0047533.ap,prai.	USPAT; EPO; JPO;	OR	OFF	2005/02/18 17:28
S1 2 "20040259296".pn. US-PGPUB; USPAT OFF 2005/02/16 17:4 S2 2 "6755909".pn. "6792029".pn. US-PGPUB; OR OFF 2005/02/16 17:4	L26	1	2001-588384.NRAN.	DERWENT	OR	OFF	2005/02/18 17:28
	S1	2	,	-	OR	OFF	2005/02/16 17:41
	S2	2	"6755909".pn. "6792029".pn.	US-PGPUB; USPAT	OR	OFF	2005/02/16 17:45

S3	8	2001kr-0030698.ap,prai. jp-62026884-\$.did. jp-04180686-\$.did. wo-9745827-\$.did.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2005/02/16 17:49
S4	1	2003-200004.NRAN.	DERWENT	OR	OFF	2005/02/16 17:51
S5	1	2004-688697.NRAN.	DERWENT	OR	OFF	2005/02/16 17:52